# DIELECTRIC STACK


## ABSTRACT

A method of forming a device is disclosed. The method includes providing a substrate and forming a device layer on the substrate having a formed thickness $T_{FD}$. A capping layer is formed on the substrate having a formed thickness $T_{FC}$. Forming the capping layer consumes a desired amount of the device layer to cause the thickness of the device layer to be about the target thickness $T_{TD}$. The thickness of the capping layer is adjusted from $T_{FC}$ to about a target thickness $T_{TC}$.


**Fig. 4**